

**Silicon Power Transistors**

**2SC4448**

**DESCRIPTION**

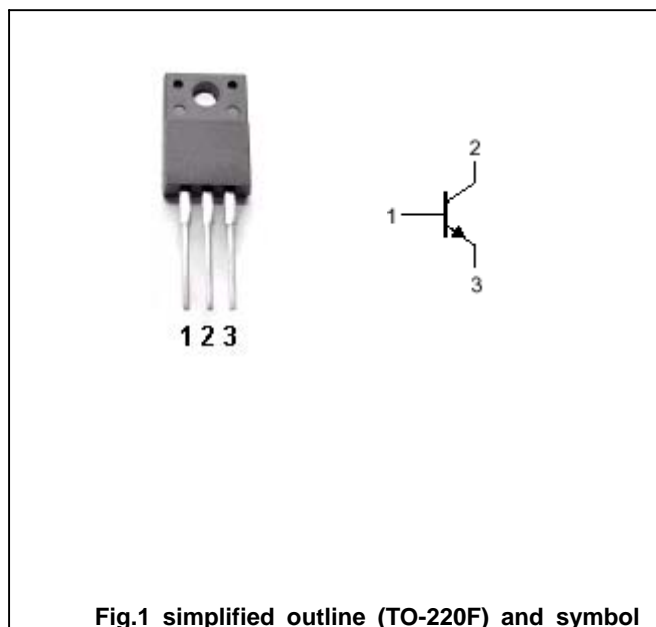
- With TO-220F package
- High voltage ,high frequency

**APPLICATIONS**

- Chroma output applications for HDTV
- Video output applications for high resolution display

**PINNING**

PIN	DESCRIPTION
1	Base
2	Collector
3	emitter



**Absolute maximum ratings(Ta=25 )**

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
$V_{CBO}$	Collector-base voltage	Open emitter	250	V
$V_{CEO}$	Collector-emitter voltage	Open base	250	V
$V_{EBO}$	Emitter-base voltage	Open collector	5	V
$I_C$	Collector current		150	mA
$I_{CM}$	Collector current-peak		300	mA
$I_B$	Base current		50	mA
$P_C$	Collector dissipation	$T_a=25$	2	W
$P_C$	Collector dissipation	$T_C=25$	10	W
$T_j$	Junction temperature		150	
$T_{stg}$	Storage temperature		-55~150	

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## CHARACTERISTICS

T<sub>j</sub>=25 unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V <sub>CEsat</sub>	Collector-emitter saturation voltage	I <sub>C</sub> =50mA I <sub>B</sub> =5mA			1.0	V
V <sub>BEsat</sub>	Base-emitter saturation voltage	I <sub>C</sub> =50mA I <sub>B</sub> =5mA			1.0	V
I <sub>CBO</sub>	Collector cut-off current	V <sub>CB</sub> =200V I <sub>E</sub> =0			100	μ A
I <sub>EBO</sub>	Emitter cut-off current	V <sub>EB</sub> =5V; I <sub>C</sub> =0			10	μ A
h <sub>FE-1</sub>	DC current gain	I <sub>C</sub> =10mA ; V <sub>CE</sub> =10V	40		200	
h <sub>FE-2</sub>	DC current gain	I <sub>C</sub> =100mA ; V <sub>CE</sub> =10V	20			
f <sub>T</sub>	Transition frequency	I <sub>C</sub> =40mA ; V <sub>CE</sub> =10V		240		MHz
C <sub>OB</sub>	Collector output capacitance	f=1MHz; V <sub>CB</sub> =30V		3.3		pF

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PACKAGE OUTLINE

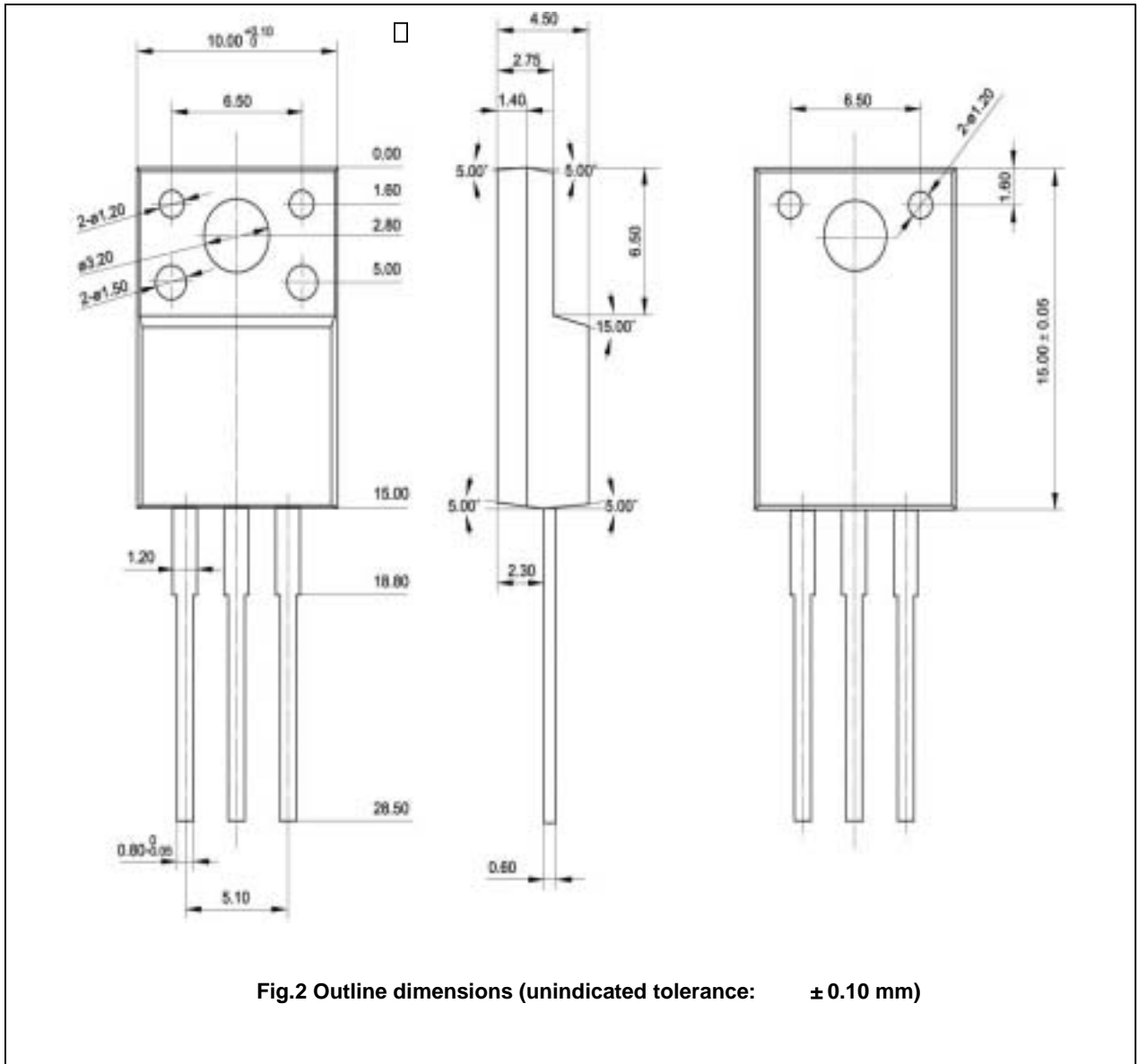


Fig.2 Outline dimensions (unindicated tolerance:  $\pm 0.10$  mm)